

Electrical transport and magnetic properties of $\text{La}_{0.85}\text{Ag}_{0.15}(\text{Mn}_{1-y}\text{Al}_y)\text{O}_3$ compounds

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Abstract . $\text{La}_{0.85}\text{Ag}_{0.15}\text{Mn}_{1-y}\text{Al}_y\text{O}_3$ compounds were prepared for $y = 0, 0.05$ and 0.10 by solid-state route. XRD patterns show that all the samples are in single phase form. Temperature variations of ac susceptibility down to 25K were measured at an ac field amplitude of 60e. All the above samples exhibit paramagnetic to ferromagnetic transitions with a decrease in ferromagnetic transition temperature (T_p) with an increase in Al doping. Temperature variation of DC electrical resistivity was measured down to 25K for all the samples. Metal-insulator (M-I) transition has been observed in all the samples with maximum transition temperature (T_p) at 285K for $y = 0$ sample.

Keywords : Ferromagnetism, (La, Ag) (Mn, Al)-O, AC Susceptibility, Manganites

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1. Introduction

Mixed valent manganites, $\text{R}_{1-x}\text{D}_x\text{MnO}_3$ (where R = Trivalent element such as, La, Pr, Nd etc and D = Divalent element, such as, Ca, Sr, Ba, Pb etc.) have drawn considerable interest in modern research due to their interesting crystal structure, magnetic and electrical transport properties [1,2]. These materials exhibit colossal magneto-resistivity (CMR) properties in the vicinity of ferromagnetic transition. Recently the monovalent doped compound has drawn attention as each doped monovalent atom can oxidize two Mn ions from Mn^{3+} to Mn^{4+} state. Thus the optimum ratio of Mn^{3+} and Mn^{4+} i.e. 67%/33% ions can be obtained by doping relatively small fraction of mono-valent atoms. Simultaneously the size mismatch distortion will be minimized due to small amount of monovalent atom doping in place of trivalent atom. There are several reports on monovalent substitutions (Na, K, Li, Ag etc.) in place of trivalent atom 'La' [3–5]. The Mn site substituted materials

are very interesting, as the behaviour of the Mn site ions are responsible for the electrical transport and magnetic behaviour of the CMR manganites. There are a few reports on substitution in Mn site by 3d transition elements (Fe, Cr, Ru, Co, Ni etc.) [6-10]. The Mn site substitution leads to change in the type of magnetic interactions between Mn and other transition elements. Mostly it has been observed that the substitution of other 3d transition elements at the Mn site leads to decrease in double exchange ferromagnetic interaction and the suppression of the long range ferromagnetic ordering and metallic properties. Mostly the studies were devoted on the substitution of magnetic transition elements in place of Mn. However, the substitutions using non-magnetic Al is very few [11-15]. The stable valency of Al is 3+, but the ionic radius is close to that of Mn^{4+} . So Al substitution is not expected to create lattice distortion.

The monovalent Ag doped samples, $La_{1-x}Ag_xMnO_3$ show ferromagnetic transition near room temperature [4,5]. We have taken the optimum doped compound $La_{0.85}Ag_{0.15}MnO_3$ and substituted Al in place of Mn site. In this report the electrical transport and magnetic properties of $La_{0.85}Ag_{0.15}Mn_{1-y}Al_yO_3$ ($y = 0 - 0.10$) has been reported.

2. Experimental details

The $La_{0.85}Ag_{0.15}Mn_{1-y}Al_yO_3$ compounds were prepared for $y = 0, 0.05$ and 0.10 by solid state route. The final sintering was carried out at $1100^\circ C$ for over 40 hrs with intermediate grindings and compaction steps. XRD patterns were recorded at room temperature using a Bruker D-8 Advance XRD machine by employing CuK_α radiation. Temperature variation of ac susceptibility was measured by mutual inductance bridge method. The primary coil was energized by a sinusoidal signal of 233 Hz. The amplitude of ac magnetic field was 60e. The in phase and out of phase susceptibility signals were measured simultaneously using a dual phase lock-in amplifier. Temperature variation of DC electrical resistivity was measured down to 25K by employing linear four probe technique. A commercial closed cycle Helium refrigerator cryostat equipped with a temperature controller was used for temperature variations down to 25K.

3. Results and discussions

All the X-ray diffraction (XRD) patterns showed that the samples were in single phase form. Typical XRD patterns recorded for $La_{0.85}Ag_{0.15}Mn_{0.90}Al_{0.10}O_3$ compound is shown in Figure 1. The XRD patterns were analyzed with the help of foolproof program based on rietveld refinement technique [16]. The XRD patterns for all the samples could be refined using $R\bar{3}c$ space group. It is consistent with those reported for $La_{0.85}Ag_{0.15}MnO_3$ [4, 5]. The refined lattice parameters and unit cell volume are listed in Table 1. These values are comparable to those of $La_{1-x}Ag_xMnO_3$ [4,5]. The lattice parameters and unit cell volume are found to be almost constant with the Al concentration. It could be due to the comparable ionic size of Al^{3+} to that of Mn^{4+} ions.

Figure 2 shows the inphase ac susceptibility, χ' versus temperature (T) plots for the samples $y = 0.0, 0.05$ and 0.10 . One can see that all the Al doped samples show

paramagnetic to ferromagnetic transitions when they are cooled. The ferromagnetic onset temperature is above the room temperature (300K) for all the samples. The transition mid-point temperature, T_c was determined from the temperature corresponding to peak in

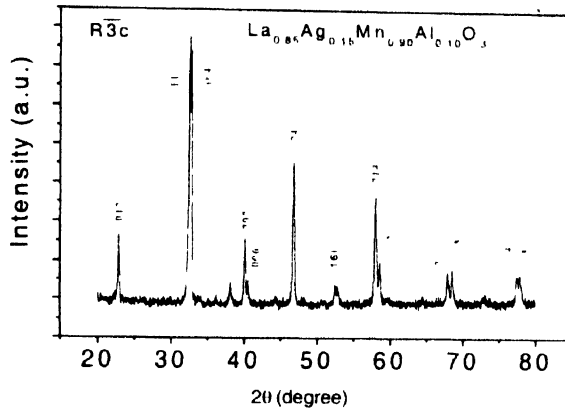


Figure 1. XRD patterns for the sample $\text{La}_{0.85}\text{Ag}_{0.15}\text{Mn}_{0.90}\text{Al}_{0.10}\text{O}_3$

$|d\chi'/dT|$ vs. T plot and, those values are tabulated in Table 1. One can see that the T_c value decreases with increase in Al concentration. Below saturation of ferromagnetic transition, the susceptibility values decrease with temperature and such behaviour has been observed by other groups. The decrease in susceptibility below ferromagnetic transition temperature can be explained as a result of loss of long range ferromagnetism and such behaviour has been reported in manganites [17].

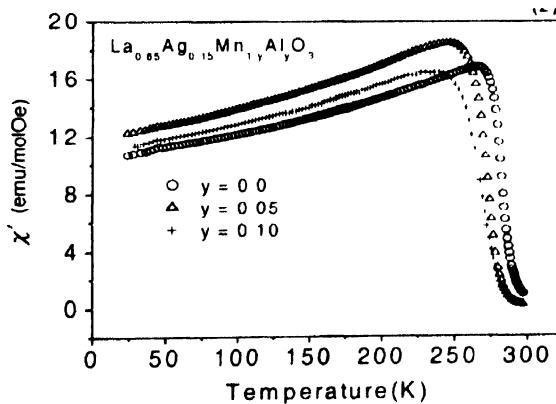


Figure 2. Temperature variation of inphase ac susceptibility (χ') of samples $y = 0.0, 0.05$ and 0.10 .

Figure 3 shows the ρ vs. T plots for $y = 0.05$ and 0.10 . One can see that all the Al doped samples exhibit metal-insulator transitions. The metal insulator transition temperature (T_{MI}) varies from 285 to 213K and these values are tabulated in Table 1. One can find that the T_{MI} value decreases with Al concentration as a result of dilution of Mn-O-Mn network and hence reduction in double exchange ferromagnetic interaction.

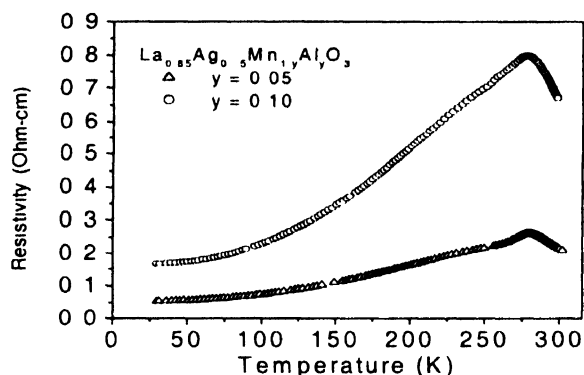


Figure 3. Temperature variation of resistivity of samples $y = 0.05$ and 0.10

Table 1. Parameters obtained from XRD, AC susceptibility and DC electrical resistivity analysis of $\text{La}_{0.85}\text{Ag}_{0.15}\text{Mn}_{1-y}\text{Al}_y\text{O}_3$ compounds

Samples \rightarrow	$y = 0.0$	$y = 0.05$	$y = 0.10$
Parameters \downarrow			
Space group	$R\bar{3}c$	$R3c$	$R3c$
a (Å)	5.520	5.519	5.518
c (Å)	13.357	13.359	13.359
V (Å ³)	352.5	352.4	352.2
T_c (K)	283	274.0	270.0
T_{MI} (K)	284	280	278

4. Conclusions

$\text{La}_{0.85}\text{Ag}_{0.15}\text{Mn}_{1-y}\text{Al}_y\text{O}_3$ compounds were prepared in single phase form for $y = 0, 0.05$ and 0.10 by solid-state route. The lattice parameters are decrease with the Al concentration due to the replacement of larger Mn^{3+} ions by smaller Al^{3+} ions. All the Al doped samples exhibit paramagnetic to ferromagnetic transitions in the temperature range 270 to 283K. All the Al doped samples exhibit metal-insulator transition with transition temperature varies from 284 to 278K.

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